

IN THE CLAIMS

Please amend the claims as shown in the marked-up copy following this amendment to read as follows.

C<sup>2</sup> 6. (Amended) The carbon-containing aluminum nitride sintered body according to claim 4,

which comprises both of crystalline carbon and amorphous carbon.

7. (Amended) The carbon-containing aluminum nitride sintered body according to claim 4,

which comprises said carbon in a total amount of 200 to 5000 ppm.

C<sup>3</sup> 9. (Amended) The carbon-containing aluminum nitride sintered body according to claim 4,

wherein its brightness defined in JIS Z 8721 is N4 or less.

C<sup>4</sup> 15. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to claim 13,

wherein the content of said carbon is from 200 to 5000 ppm.

C<sup>5</sup> 17. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to claim 13,

wherein its brightness defined in JIS Z 8721 is N4 or less.

18. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to claim 13,

wherein:

said conductor is an electrostatic electrode; and

said ceramic substrate functions as an electrostatic chuck.

19. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to claim 13,

wherein:

said conductor is a resistance heating element; and

said ceramic substrate functions as a hot plate.

20. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to claim 13,

wherein:

said conductor is formed: on a surface of the ceramic substrate; and inside the ceramic substrate;

said inside conductor is at least one of a guard electrode and a ground electrode; and

said ceramic substrate functions as a wafer prober.

21. (Amended) A carbon-containing aluminum nitride sintered body according to claim 4,

wherein:

said matrix contains a sintering aid comprising at least one of an alkali metal oxide, an alkali earth metal oxide, and a rare earth oxide; and,

its brightness defined in JIS Z 8721 is N4 or less.

22. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to claim 14,

wherein:

said ceramic substrate contains a sintering aid comprising at least one of an alkali metal oxide, an alkali earth metal oxide, and a rare earth oxide; and,

its brightness defined in JIS Z 8721 is N4 or less.

25. (Amended) The carbon-containing aluminum nitride sintered body according to claim 23,

wherein the content of said carbon is from 200 to 5000 ppm.

26. (Amended) The carbon-containing aluminum nitride sintered body according to claim 23,

wherein said matrix contains a sintering aid comprising at least one of an alkali metal oxide, an alkali earth metal oxide, and a rare earth oxide.

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Please add the following new claims.

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27. (New) A carbon-containing aluminum nitride sintered body comprising: carbon whose peak cannot be detected on its X-ray diffraction chart or whose peak is below its detection limit thereon; in a matrix made of aluminum nitride.

28. (New) The carbon-containing aluminum nitride sintered body according to claim 27,

wherein: said carbon whose peak cannot be detected on its X-ray diffraction chart or whose peak is below its detection limit thereon, is at least one of amorphous carbon, and carbon forming solid solution in the phase of aluminum nitride crystal.

29. (New) The carbon-containing aluminum nitride sintered body according to claim 27, wherein the content of said carbon is from 200 to 5000 ppm.

30. (New) The carbon-containing aluminum nitride sintered body according to claim 4,

wherein said matrix contains a sintering aid comprising at least one of an alkali metal oxide, an alkali earth metal oxide, and a rare earth oxide.

31. (New) A ceramic substrate for a semiconductor-producing/examining device,

wherein: a ceramic substrate comprising carbon whose peak cannot be detected on its X-ray diffraction chart or whose peak is below its detection limit thereon, is provided with a conductor.

32. (New) The ceramic substrate for the semiconductor-producing/examining device according to claim 31,

87 wherein: said carbon whose peak cannot be detected on its X-ray diffraction chart or whose peak is below its detection limit thereon, is at least one of amorphous carbon, and carbon forming solid solution in the phase of ceramic crystal.

33. (New) The ceramic substrate for the semiconductor-producing/examining device according to claim 31, wherein the content of said carbon is from 200 to 5000 ppm.

34. (New) The ceramic substrate for the semiconductor-producing/examining device according to claim 13,

wherein said ceramic substrate contains a sintering aid comprising at least one of an alkali metal oxide, an alkali earth metal oxide, and a rare earth oxide.

35. (New) The carbon-containing aluminum nitride sintered body according to claim 27,

wherein said matrix contains a sintering aid comprising at least one of an alkali metal oxide, an alkali earth metal oxide, and a rare earth oxide.

36. (New) The ceramic substrate for the semiconductor-producing/examining device according to claim 31,

wherein said ceramic substrate contains a sintering aid comprising at least one of an alkali metal oxide, an alkali earth metal oxide, and a rare earth oxide.

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REMARKS